

In the Claims:

1. (Currently Amended) A magnetic memory comprising:
a plurality of digit lines;
a plurality of bit lines, ~~wherein the digit lines and the bit lines intersect each other at an oblique angle; and~~
a plurality of magnetic tunnel junctions (MTJs) between the bit lines and the digit lines arranged in rows and columns at overlap points between the bit lines and the digit lines,
wherein each of bit lines is coupled to MTJs in a respective column and each of the digit lines is coupled to MTJs in a respective row, and
wherein the digit lines and the bit lines intersect each other at an oblique angle, and the digit lines and/or the bit lines each have a zigzag shape that reverses direction with respect to itself.
2. (Original) The magnetic memory of claim 1, wherein the digit lines and the bit lines intersect each other at an oblique angle of between 15° to 75°.
3. (Original) The magnetic memory of claim 1, wherein the MTJs are directly connected to the bit lines, and are spaced apart from the digit lines.
4. (Currently Amended) The magnetic memory of claim 1, further comprising a plurality of cell transistors arranged along the rows and columns, ~~wherein the cell transistors are arrayed along a row direction and a column direction,~~ wherein the cell transistors each comprise a gate electrode, a source region and a drain region, and wherein the gate electrodes of the cell transistors in a respective row are connected to each other through a plurality of word lines to form a word line, and wherein the drain region is electrically connected to a respective MTJ.

5. (Currently Amended) The magnetic memory of claim 4, wherein the digit lines are parallel to the word lines, and each of the bit lines intersect the word lines at an oblique angle has a zigzag shape that reverses direction with respect to itself and is electrically connected to the MTJs arranged along a diagonal direction with respect to the rows and columns.

6. (Currently Amended) The magnetic memory of claim ~~[[5]]~~ 4, wherein the bit lines ~~diagonally connect the drain regions of the cell transistors to each other~~ intersect the word lines, and each of the digit lines has a zigzag shape that reverses direction with respect to itself and is coupled to the MTJs arranged along a diagonal direction with respect to the rows and columns.

7. (Currently Amended) The magnetic memory of claim ~~[[5]]~~ 4, wherein the digit lines are parallel to the word lines, and each of the bit lines has a zigzag to connect the drain regions of the cell transistors to each other shape that reverses direction with respect to itself and overlaps the MTJs arranged along a diagonal direction with respect to the rows and columns.

8. (Currently Amended) The magnetic memory of claim 4, wherein the bit lines intersect the word lines ~~perpendicularly, and the digit lines intersect the word lines at an oblique angle~~ , and each of the digit lines has a zigzag shape that reverses direction with respect to itself and overlaps the MTJs arranged along a diagonal direction with respect to the rows and columns.

9. (Currently Amended) The magnetic memory of claim ~~[[8]]~~ 4, wherein ~~the digit lines diagonally intersect the cell transistors~~ the bit lines intersect the word lines, and each of the digit lines has a zigzag shape that reverses direction with respect to itself and intersects a respective word line in a zigzag pattern.

10. (Currently Amended) The magnetic memory of claim ~~[[8]]~~ 5, wherein ~~the digit lines intersect the cell transistors in a zigzag pattern~~ the MTJs each have a parallelogram shape with two angles greater than approximately 90° and two angles less than approximately 90°.

11. (Currently Amended) The magnetic memory of claim ~~11~~ 10, wherein ~~the fixed layer comprises a lower ferromagnetic film, a ruthenium film and an upper ferromagnetic film~~ two longer opposing sides of the parallelogram shaped MTJs are parallel to the bit lines.

12. (Canceled).

13. (Currently Amended) The magnetic memory of claim ~~[[1]]~~ 6, wherein the MTJs ~~comprise a pinning layer, a fixed layer, an insulating layer and a free layer~~ each have a parallelogram shape with two angles greater than approximately 90° and two angles less than approximately 90°.

14. (Currently Amended) The magnetic memory of claim ~~[[1]]~~ 13, wherein ~~the MTJs have a rectangular shape~~ two longer opposing sides of the parallelogram shaped MTJs are parallel to the digit lines.

15-28. (Canceled).

29. (New) The magnetic memory of claim 1, wherein the plurality of MTJs coupled by the bit lines and digit lines are arranged in a rectangular shape.

30. (New) The magnetic memory of claim 1, wherein the digit lines and the bit lines intersect each other at an oblique angle of between 60° and 90°.

31. (New) The magnetic memory of claim 1, wherein the digit lines and/or the bit lines have a repeating "W" shape.

32. (New) The magnetic memory of claim 1, wherein the digit lines and/or the bit lines have a repeating "V" shape.